Zbigniew Galazka

List of Publications by Year
in descending order

157 papers	7,800 citations	71061 41 h-index	53190 85 g-index
160 all docs	160 docs citations	160 times ranked	4321 citing authors

#	Article	IF	Citations
1	On the bulk Î²-Ga2O3 single crystals grown by the Czochralski method. Journal of Crystal Growth, 2014, 404, 184-191.	0.7	556
2	3.8-MV/cm Breakdown Strength of MOVPE-Grown Sn-Doped <inline-formula> <tex-math notation="LaTeX">$eta $ </tex-math> </inline-formula>-Ga₂O₃MOSFETs. IEEE Electron Device Letters, 2016, 37, 902-905.	2.2	468
3	Electrical properties of <i>Î²</i>-Ga2O3 single crystals grown by the Czochralski method. Journal of Applied Physics, 2011, 110, .	1.1	442
4	Czochralski growth and characterization of Î²â€Ga₂O₃ single crystals. Crystal Research and Technology, 2010, 45, 1229-1236.	0.6	378
5	Enhancement-mode Ga2O3 wrap-gate fin field-effect transistors on native (100) <i>Î²</i>-Ga2O3 substrate with high breakdown voltage. Applied Physics Letters, 2016, 109, .	1.5	298
6	Schottky barrier height of Au on the transparent semiconducting oxide <i>Î²</i>-Ga2O3. Applied Physics Letters, 2012, 101, .	1.5	293
7	High-voltage field effect transistors with wide-bandgap <i>Î²</i>-Ga2O3 nanomembranes. Applied Physics Letters, 2014, 104, .	1.5	288
8	Î²-Ga₂O₃ for wide-bandgap electronics and optoelectronics. Semiconductor Science and Technology, 2018, 33, 113001.	1.0	285
9	Scaling-Up of Bulk Î²-Ga₂O₃Single Crystals by the Czochralski Method. ECS Journal of Solid State Science and Technology, 2017, 6, Q3007-Q3011.	0.9	280
10	Experimental electronic structure of In₂O₃and Ga₂O₃. New Journal of Physics, 2011, 13, 085014.	1.2	273
11	eta -Ga2O3 MOSFETs for Radio Frequency Operation. IEEE Electron Device Letters, 2017, 38, 790-793.	2.2	248
12	Homoepitaxial growth of Î²â€Ga₂O₃ layers by metalâ€organic vapor phase epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 27-33.	0.8	170
13	Recent progress in the growth of Î²-Ga2O3 for power electronics applications. Materials Science in Semiconductor Processing, 2018, 78, 132-146.	1.9	168
14	The electronic structure of Î²-Ga2O3. Applied Physics Letters, 2010, 97, .	1.5	146
15	Electrical compensation by Ga vacancies in Ga2O3 thin films. Applied Physics Letters, 2015, 106, .	1.5	142
16	Structural properties of Si-doped Î²-Ga2O3 layers grown by MOVPE. Journal of Crystal Growth, 2014, 401, 665-669.	0.7	133
17	Epitaxial stabilization of pseudomorphic Î±-Ga₂O₃on sapphire (0001). Applied Physics Express, 2015, 8, 011101.	1.1	104
18	On the nature and temperature dependence of the fundamental band gap of In₂O₃. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 54-58.	0.8	96

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19	Growth of bulk Î²-Ga2O3 single crystals by the Czochralski method. Journal of Applied Physics, 2022, 131, .	1.1	84
20	Doping of Czochralski-grown bulk Î²-Ga2O3 single crystals with Cr, Ce and Al. Journal of Crystal Growth, 2018, 486, 82-90.	0.7	83
21	Many-electron effects on the dielectric function of cubic<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>In</mml:mi><mml:mn>2</mml:mn></mml:n mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>: Effective electron mass, band nonparabolicity, band gap renormalization, and Burstein-Moss shift. Physical Review B, 2016, 93, .	1.1	82
22	Substrate-orientation dependence of Î²-Ga2O3 (100), (010), (001), and (2Â¯01) homoepitaxy by indium-mediated metal-exchange catalyzed molecular beam epitaxy (MEXCAT-MBE). APL Materials, 2020, 8, .	2.2	80
23	Temperature-dependent thermal conductivity in Mg-doped and undoped<i>Î²</i>-Ga₂O₃bulk-crystals. Semiconductor Science and Technology, 2015, 30, 024006.	1.0	79
24	Czochralski-grown bulk Î²-Ga2O3 single crystals doped with mono-, di-, tri-, and tetravalent ions. Journal of Crystal Growth, 2020, 529, 125297.	0.7	78
25	Evolution of planar defects during homoepitaxial growth of <i>Î²</i>-Ga2O3 layers on (100) substratesâ€"A quantitative model. Journal of Applied Physics, 2016, 120, .	1.1	75
26	Ultra-wide bandgap, conductive, high mobility, and high quality melt-grown bulk ZnGa2O4 single crystals. APL Materials, 2019, 7, .	2.2	74
27	Scintillation properties of selected oxide monocrystals activated with Ce and Pr. Optical Materials, 2006, 28, 85-93.	1.7	73
28	Step-flow growth in homoepitaxy of Î²-Ga2O3 (100)â€"The influence of the miscut direction and faceting. APL Materials, 2019, 7, .	2.2	73
29	Influence of incoherent twin boundaries on the electrical properties of Î²-Ga2O3 layers homoepitaxially grown by metal-organic vapor phase epitaxy. Journal of Applied Physics, 2017, 122, .	1.1	69
30	Melt growth, characterization and properties of bulk In2O3 single crystals. Journal of Crystal Growth, 2013, 362, 349-352.	0.7	62
31	Step flow growth of <i>Î²</i>-Ga2O3 thin films on vicinal (100) <i>Î²</i>-Ga2O3 substrates grown by MOVPE. Applied Physics Letters, 2020, 116, .	1.5	59
32	Static Dielectric Constant of <i>Î²</i>-Ga₂O₃ Perpendicular to the Principal Planes (100), (010), and (001). ECS Journal of Solid State Science and Technology, 2019, 8, Q3083-Q3085.	0.9	58
33	MgGa₂ O₄ as a new wide bandgap transparent semiconducting oxide: growth and properties of bulk single crystals. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1455-1460.	0.8	56
34	Bulk Single Crystalâ€Like Structural and Magnetic Characteristics of Epitaxial Spinel Ferrite Thin Films with Elimination of Antiphase Boundaries. Advanced Materials, 2017, 29, 1701222.	11.1	54
35	A novel crystal growth technique from the melt: Levitation-Assisted Self-Seeding Crystal Growth Method. Journal of Crystal Growth, 2014, 388, 61-69.	0.7	49
36	Near valence-band electronic properties of semiconducting<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î²</mml:mi><mml:msub><mml:mrow><mml:mo>â^'</mm mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>(100) single crystals. Physical Review B, 2015, 92, .	1.1	47

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37	Bulk single crystals of Î²-Ga2O3 and Ga-based spinels as ultra-wide bandgap transparent semiconducting oxides. Progress in Crystal Growth and Characterization of Materials, 2021, 67, 100511.	1.8	47
38	Growth, characterization, and properties of bulk SnO₂ single crystals. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 66-73.	0.8	46
39	Surface properties of annealed semiconducting Î²-Ga2O3 (1 0 0) single crystals for epitaxy. Applied Surface Science, 2015, 349, 368-373.	3.1	46
40	Numerical Modelling of the Czochralski Growth of Î²-Ga2O3. Crystals, 2017, 7, 26.	1.0	46
41	Large-lattice-parameter perovskite single-crystal substrates. Journal of Crystal Growth, 2017, 457, 137-142.	0.7	42
42	Effect of metal contacts on (100) Î²-Ga2O3 Schottky barriers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	42
43	Temperature-dependent optical absorption of SrTiO₃. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1880-1887.	0.8	41
44	Effect of heat treatment on properties of melt-grown bulk In₂O₃single crystals. CrystEngComm, 2013, 15, 2220-2226.	1.3	40
45	<inline-formula> <tex-math notation="LaTeX">eta</tex-math> </inline-formula>-Ga₂O₃Solid-State Devices for Fast Neutron Detection. IEEE Transactions on Nuclear Science, 2017, 64, 1574-1579.	1.2	40
46	A new approach to free-standing GaN using Î²-Ga2O3 as a substrate. CrystEngComm, 2012, 14, 8536.	1.3	37
47	Ti- and Fe-related charge transition levels in Î²âˆ’Ga2O3. Applied Physics Letters, 2020, 116, .	1.5	37
48	The surface band structure of Î²-Ga₂O₃. Journal of Physics: Conference Series, 2011, 286, 012027.	0.3	35
49	Temperature-dependent thermal conductivity and diffusivity of a Mg-doped insulating<i>Î²</i>-Ga₂O₃single crystal along [100], [010] and [001]. Semiconductor Science and Technology, 2016, 31, 125006.	1.0	33
50	High field-emission current density from Î²-Ga2O3 nanopillars. Applied Physics Letters, 2019, 114, .	1.5	33
51	Compensating vacancy defects in Sn- and Mg-doped<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>In</mml:mi><mml:mn>2</mml:mn></mm mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2014, 90, .	1.1	32
52	Enhanced magnon spin transport in NiFe2O4 thin films on a lattice-matched substrate. Applied Physics Letters, 2018, 113, .	1.5	31
53	Two inch diameter, highly conducting bulk <i>Î²</i> -Ga2O3 single crystals grown by the Czochralski method. Applied Physics Letters, 2022, 120, .	1.5	31
54	Atomic signatures of local environment from core-level spectroscopy in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î²</mml:mi><mml:mtext>âˆ’</mml:mtext><mml:msub>< mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2016, 94, .	1.1	28

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55	Melt growth and properties of bulk BaSnO₃single crystals. Journal of Physics Condensed Matter, 2017, 29, 075701.	0.7	28
56	Bulk Î²-Ga2O3 single crystals doped with Ce, Ce+Si, Ce+Al, and Ce+Al+Si for detection of nuclear radiation. Journal of Alloys and Compounds, 2020, 818, 152842.	2.8	28
57	Coloration and oxygen vacancies in wide band gap oxide semiconductors: Absorption at metallic nanoparticles induced by vacancy clusteringâ€”A case study on indium oxide. Journal of Applied Physics, 2014, 115, 053504.	1.1	27
58	The anisotropic quasi-static permittivity of single-crystal <i>Î²</i> -Ga2O3 measured by terahertz spectroscopy. Applied Physics Letters, 2020, 117, .	1.5	27
59	Impact of chamber pressure and Si-doping on the surface morphology and electrical properties of homoepitaxial (100) Î²-Ga₂O₃thin films grown by MOVPE. Journal Physics D: Applied Physics, 2021, 54, 034003.	1.3	26
60	An analysis of and a model for spiral growth of Czochralski-grown oxide crystals with high melting point. Journal of Crystal Growth, 2011, 335, 138-147.	0.7	25
61	Temperatureâ€dependent electrical characterization of exfoliated <i>Î²</i>â€Ga₂O₃ micro flakes. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 543-549.	0.8	25
62	Thin film transistors based on ultra-wide bandgap spinel ZnGa2O4. Applied Physics Letters, 2020, 116, .	1.5	24
63	Î²-Ga2O3:Ce as a fast scintillator: An unclear role of cerium. Radiation Measurements, 2019, 121, 49-53.	0.7	23
64	<i>(Invited)</i> Electrical Properties of (100) Î²-Ga₂O₃ Schottky Diodes with Four Different Metals. ECS Transactions, 2019, 92, 71-78.	0.3	22
65	Semiconductor scintillator development: Pure and doped Î²-Ga2O3. Optical Materials, 2020, 105, 109856.	1.7	22
66	Fast homoepitaxial growth of (100) Î²-Ga2O3 thin films via MOVPE. AIP Advances, 2021, 11, .	0.6	22
67	On the influence of inversion on thermal properties of magnesium gallium spinel. Crystal Research and Technology, 2015, 50, 961-966.	0.6	21
68	Longitudinal phonon plasmon mode coupling in <i> Î² </i>-Ga2O3. Applied Physics Letters, 2019, 114, .	1.5	21
69	Optical properties of In₂O₃ from experiment and first-principles theory: influence of lattice screening. New Journal of Physics, 2018, 20, 053016.	1.2	20
70	Pseudomorphic spinel ferrite films with perpendicular anisotropy and low damping. Applied Physics Letters, 2018, 113, .	1.5	18
71	Luminescence and scintillation properties of YAG:Pr. IEEE Transactions on Nuclear Science, 2002, 49, 926-930.	1.2	17
72	Offcut-related step-flow and growth rate enhancement during (100) <i>Î²</i> -Ga2O3 homoepitaxy by metal-exchange catalyzed molecular beam epitaxy (MEXCAT-MBE). Applied Physics Letters, 2020, 117, .	1.5	17

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73	Heat Transfer and Fluid Flow during Growth of Y3Al5O12 Single Crystals using the Czochralski Method. Crystal Research and Technology, 2000, 35, 1263-1278.	0.6	16
74	Growth of wurtzite InN on bulk In2O3(111) wafers. Applied Physics Letters, 2012, 101, .	1.5	16
75	Resonant photoemission at the O1s threshold to characterize In2O3 single crystals. Thin Solid Films, 2014, 555, 53-56.	0.8	16
76	MOVPE growth of violet GaN LEDs on Î²-Ga2O3 substrates. Journal of Crystal Growth, 2017, 478, 212-215.	0.7	16
77	Role of interface quality for the spin Hall magnetoresistance in nickel ferrite thin films with bulk-like magnetic properties. Applied Physics Letters, 2019, 115, .	1.5	16
78	Influence of internal radiation on the heat transfer during growth of YAG single crystals by the Czochralski method. Crystal Research and Technology, 2003, 38, 859-867.	0.6	15
79	Top-seeded solution growth of SrTiO3 crystals and phase diagram studies in the SrOâ€"TiO2 system. CrystEngComm, 2014, 16, 1735.	1.3	15
80	Thermal expansion of single-crystalline <i>Î²</i>-Ga2O3 from RT to 1200â€‰K studied by synchrotron-based high resolution x-ray diffraction. Applied Physics Letters, 2018, 113, .	1.5	15
81	Tailoring the scintillation properties of Î²-Ga₂O₃ by doping with Ce and codoping with Si. Optical Materials Express, 2019, 9, 3738.	1.6	15
82	Growth of SrTiO₃bulk single crystals using edge-defined film-fed growth and the Czochralski methods. CrystEngComm, 2015, 17, 4662-4668.	1.3	14
83	Theoretical and experimental investigation of the electronic properties of the wide band-gap transparent semiconductor MgGa2O4. Physical Review B, 2018, 97, .	1.1	14
84	Indium incorporation in homoepitaxial Î²-Ga2O3 thin films grown by metal organic vapor phase epitaxy. Journal of Applied Physics, 2019, 125, .	1.1	14
85	Anisotropic optical properties of highly doped rutile SnO2: Valence band contributions to the Burstein-Moss shift. APL Materials, 2019, 7, .	2.2	14
86	Raman scattering in heavily donor doped <i>Î²</i> -Ga2O3. Applied Physics Letters, 2020, 117, .	1.5	14
87	<title>Comparison of structural and optical properties of LiNbO3 single crystals doped with Pr3+, Yb3+, and Pr3+ + Yb3+ ions</title>. , 1997, , .		13
88	Comparative study of the electronic structures of the In and<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>Sn</mml:mi><mml:mo>/</mml:mo><mml:mi>In</mml:mi><mml:mrow /><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>(111) interfaces. Physical Review B, 2016, 93, .	1.1	13
89	Temperature dependence of the Seebeck coefficient of epitaxial Î²-Ga2O3 thin films. APL Materials, 2019, 7, 022526.	2.2	13
90	Enhancement in Thermally Generated Spin Voltage at the Interfaces between <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Pd</mml:mi></mml:math> and <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mrow><mml:mi>Ni</mml:mi><mml:mi>Fe</mml:mi></mml:mrow><mml:mn>2</mml:mn></mml: mathvariant="normal">O</mml:mi><mml:mn>4</mml:mn></mml:msub></mml:math> Films Grown on Lat	1.5	13

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91	<title>Radio- and VUV-excited luminescence of YAP:Ce, YAP:Pr and YAG:Pr</title>. , 2001, , .		12
92	Inâ€gap states of In₂O₃ single crystals investigated by scanning tunneling spectroscopy. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 59-65.	0.8	12
93	Schottky contact by Ag on In2O3 (111) single crystals. Applied Physics Letters, 2014, 105, .	1.5	12
94	Influence of oxygen partial pressure on SrTiO₃bulk crystal growth from non-stoichiometric melts. CrystEngComm, 2015, 17, 3224-3234.	1.3	12
95	Growth mode evolution during (100)-oriented <i>Î²</i>-Ga₂O₃ homoepitaxy. Nanotechnology, 2018, 29, 395705.	1.3	12
96	Vectorial observation of the spin Seebeck effect in epitaxial NiFe2O4 thin films with various magnetic anisotropy contributions. Applied Physics Letters, 2019, 114, .	1.5	12
97	Electrical conductivity tensor of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î²</mml:mi><mml:mo>â^'</mml:mo><mml:msub><mml:m mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> analyzed by van der Pauw measurements: Inherent anisotropy, off-diagonal element, and the impact of grain boundaries. Physical Review Materials, 2019, 3, .	0.9	12
98	SnO/Î²-Ga2O3 heterojunction field-effect transistors and vertical pâ€"n diodes. Applied Physics Letters, 2022, 120, .	1.5	12
99	Hall and Seebeck measurements estimate the thickness of a (buried) carrier system: Identifying interface electrons in In-doped SnO2 films. Applied Physics Letters, 2015, 107, .	1.5	11
100	Interplay of cation ordering and thermoelastic properties of spinel structure MgGa2O4. Journal of Applied Physics, 2018, 124, .	1.1	11
101	Charge carrier density, mobility, and Seebeck coefficient of melt-grown bulk ZnGa2O4 single crystals. AIP Advances, 2020, 10, .	0.6	11
102	Structural and magnetic properties of NiFe2O4 thin films grown on isostructural lattice-matched substrates. Applied Physics Letters, 2021, 118, .	1.5	11
103	Optical phonon modes, static and high-frequency dielectric constants, and effective electron mass parameter in cubic In2O3. Journal of Applied Physics, 2021, 129, .	1.1	11
104	The inherent transport anisotropy of rutile tin dioxide (SnO2) determined by van der Pauw measurements and its consequences for applications. Applied Physics Letters, 2018, 112, 092105.	1.5	10
105	Transport Properties and Finite Size Effects in Î²-Ga2O3 Thin Films. Scientific Reports, 2019, 9, 13149.	1.6	10
106	Czochralski Method. Springer Series in Materials Science, 2020, , 15-36.	0.4	10
107	A consistent picture of excitations in cubic BaSnO3 revealed by combining theory and experiment. Communications Materials, 2022, 3, .	2.9	10
108	Oxygen diffusion in Î²-Ga2O3 single crystals at high temperatures. Applied Physics Letters, 2021, 119, .	1.5	10

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109	Fast atom diffraction from a Î²-Ga2O3(100) surface. Applied Physics Letters, 2014, 105, 051603.	1.5	9
110	A spectroscopic comparison of IGZO thin films and the parent In₂O₃, Ga₂O₃, and ZnO single crystals. Materials Research Express, 2016, 3, 106302.	0.8	9
111	Photosensitization of Natural and Synthetic SnO₂ Single Crystals with Dyes and Quantum Dots. Journal of Physical Chemistry C, 2016, 120, 15735-15742.	1.5	9
112	Photoelectron spectroscopic study of electronic state and surface structure of In2O3 single crystals. Applied Physics Express, 2017, 10, 011102.	1.1	9
113	Thermal conductivity of bulk <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>In</mml:mi><mml:mn>2</mml:mn></mm mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> single crystals. Physical Review Materials, 2021, 5, .	0.9	9
114	Zinc gallate spinel dielectric function, band-to-band transitions, and Î“-point effective mass parameters. Applied Physics Letters, 2021, 118, .	1.5	9
115	Melt Growth and Physical Properties of Bulk LaInO 3 Single Crystals. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100016.	0.8	9
116	Experimental Hall electron mobility of bulk single crystals of transparent semiconducting oxides. Journal of Materials Research, 2021, 36, 4746-4755.	1.2	9
117	Perspectives for high resolution and high light output LuAP:Ce crystals. IEEE Transactions on Nuclear Science, 2005, 52, 1823-1829.	1.2	8
118	Transparent Semiconducting Oxides. , 0, , .		8
119	Experimental Study of Interface Inversion of Tb3ScxAl5-xO12 Single Crystals Grown by the Czochralski Method. Crystal Research and Technology, 2002, 37, 407-413.	0.6	7
120	Photoelectron spectroscopic study of electronic states and surface structure of an in situ cleaved In2O3 (111) single crystal. Japanese Journal of Applied Physics, 2019, 58, SDDG06.	0.8	7
121	Electroluminescence of Cr3+ and pseudo-Stark effect in Î²-Ga2O3 Schottky barrier diodes. Journal of Applied Physics, 2019, 126, 213104.	1.1	7
122	Resonant electronic Raman scattering from Ir4+ ions in <i>Î²</i>-Ga2O3. Journal of Applied Physics, 2022, 131, .	1.1	7
123	Electron paramagnetic resonance studies of cobalt and rare-earth impurity ions in YAlO3. Journal of Physics Condensed Matter, 2006, 18, 4751-4761.	0.7	6
124	Photoelectron spectroscopic study on electronic state and electrical properties of SnO2 single crystals. Japanese Journal of Applied Physics, 2019, 58, 080903.	0.8	6
125	Fingerprints of optical absorption in the perovskite LaInO3 : Insight from many-body theory and experiment. Physical Review B, 2021, 103, .	1.1	6
126	Recent progress in the development of Î²-Ga₂O₃ scintillator crystals grown by the Czochralski method. Optical Materials Express, 2021, 11, 2488.	1.6	6

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127	Impact of substrate nitridation on the growth of InN on In 2 O 3 (111) by plasma-assisted molecular beam epitaxy. Applied Surface Science, 2016, 369, 159-162.	3.1	5
128	Top-seeded solution growth of SrTiO 3 single crystals virtually free of mosaicity. Journal of Crystal Growth, 2017, 468, 305-310.	0.7	5
129	Brillouin zone center phonon modes in ZnGa2O4. Applied Physics Letters, 2020, 117, .	1.5	5
130	Heading for brighter and faster Î²-Ga2O3 scintillator crystals. Optical Materials: X, 2022, 15, 100157.	0.3	5
131	Growth and optical properties of Nd:YVO 4 laser crystals. , 1999, 3724, 324.		4
132	Vacancy complexes in Sb-doped SnO2. , 2014, , .		4
133	Cation vacancies and electrical compensation in Sb-doped thin-film SnO₂and ZnO. Semiconductor Science and Technology, 2015, 30, 024011.	1.0	4
134	Polaron character of the near-E _F band of cleaved In ₂ O ₃ (111) single crystals. Europhysics Letters, 2016, 113, 26003.	0.7	4
135	Deep-level noise characterization of MOVPE-grown <i>Î²</i> -Ga2O3. Applied Physics Letters, 2019, 115, .	1.5	4
136	Signatures of free carriers in Raman spectra of cubic In₂O₃. Semiconductor Science and Technology, 2020, 35, 015017.	1.0	4
137	Elevated temperature spectroscopic ellipsometry analysis of the dielectric function, exciton, band-to-band transition, and high-frequency dielectric constant properties for single-crystal ZnGa2O4. Applied Physics Letters, 2022, 120, .	1.5	4
138	Development of a cryogenic In<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" id="d1e413" altimg="si88.svg"><mml:msub><mml:mrow /><mml:mrow><mml:mn>2</mml:mn></mml:mrow></mml:msub></mml:math>O<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" id="d1e421" altimg="si89.svg"><mml:msub><mml:mrow /><mml:mrow><mml:mn>3</mml:mn></mml:mrow></mml:msub></mml:math> calorimeter to measure t	0.7	4
139	Analysis of Thermal Shock during Rapid Crystal Extraction from Melts. Crystal Research and Technology, 1999, 34, 635-640.	0.6	3
140	Growth and Optical Properties of Doped LiTaO3 Single Crystals. Crystal Research and Technology, 2001, 36, 127-134.	0.6	3
141	Time-resolved optical absorption in YAlO3 crystals. Radiation Measurements, 2004, 38, 371-374.	0.7	3
142	Growth Techniques for Bulk ZnO and Related Compounds. Materials Research Society Symposia Proceedings, 2012, 1394, 32.	0.1	3
143	High melting point oxides â€“ a challenge for crystal growth. Crystal Research and Technology, 2012, 47, 247-252.	0.6	3
144	Growth Measures to Achieve Bulk Single Crystals of Transparent Semiconducting and Conducting Oxides. , 2015, , 209-240.		3

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145	Stability and solubility of members of tin perovskites in the schoenfliesite subgroup, <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si224.svg"><mml:mrow><mml:mo>â–¡</mml:mo><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>(BSn<mml:math) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 732	0.7	3
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147	<title>Growth and basic investigations of LiNbO3 single crystals doped with Dy3+ ions</title>. , 1997, , .		1
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